L Number	Hits	Search Text	DB	Time stamp
1	53	("MIS") same ((("C-V") or (CV)) near3 characteristic$5) same capacit$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/18 10:30
2	1	("6636073").PN.	USPAT; US-PGPUB	2004/03/18 10:35
3	3	(("5107137") or ("5175445") or ("6177826")).PN.	USPAT; US-PGPUB	2004/03/18 10:36
4	1	6636073.pn. and MIS	USPAT; US-PGPUB	2004/03/18 10:37
5	0	6636073.URPN.	USPAT	2004/03/18 10:38
6	0	6636073.URPN.	USPAT	2004/03/18 10:38
7	0	6636073.URPN.	USPAT	2004/03/18 10:38
8	0	6392623.URPN.	USPAT	2004/03/18 10:40
-	46	(("metal/insulator/semiconductor") or ("metal-insulator-semiconductor")or ("MIS")) same ((("C-V") or (CV)) near3 characteristic$5) same capacit$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/18 10:26
-	37	(("metal/insulator/semiconductor") or ("metal-insulator-semiconductor")or ("MIS")) and ("LCR" adj meter)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/09 11:46
-	1	"4083254".PN.	USPAT; US-PGPUB	2002/12/09 11:50
-	1	"4322979".PN.	USPAT; US-PGPUB	2002/12/09 11:50
-	1	"4681451".PN.	USPAT; US-PGPUB	2002/12/09 11:50
-	72	(("metal/insulator/semiconductor") or ("metal-insulator-semiconductor")or ("MIS")) same ((("C-V") or (CV) or (capacit$4 adj voltage) or (capacit$4-voltage) or (capacit$4/voltage)) near3 characteristic$5) same capacit$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/09 14:03
-	3	5701088.bi,uref.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/09 13:37
-	4	"6177826"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/09 12:34
-	23	"5175445"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/09 12:35
-	3	(("6177826") or ("5175445") or ("5107137")).PN.	USPAT; US-PGPUB	2002/12/09 12:35
-	14	5233291.bi,uref.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/09 14:00
-	2	5233291.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/10 10:03
-	1	"5065103".PN.	USPAT; US-PGPUB	2002/12/09 14:00
-	1	"4992728".PN.	USPAT; US-PGPUB	2002/12/09 14:01

–	1	"4941753".PN.	USPAT; US-PGPUB	2002/12/09 14:01
–	1	"4891584".PN.	USPAT; US-PGPUB	2002/12/09 14:01
–	154	(("metal/insulator/semiconductor") or ("metal-insulator-semiconductor")or ("MIS")) same (("C-V") or (CV) or (capacit$4 adj voltage) or (capacit$4-voltage) or (capacit$4/voltage)) and characteristic$5 and capacit$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/09 14:05
–	155	(("metal/insulator/semiconductor") or ("metal-insulator-semiconductor")or ("MIS") or ("MAIS")) same (("C-V") or (CV) or (capacit$4 adj voltage) or (capacit$4-voltage) or (capacit$4/voltage)) and characteristic$5 and capacit$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/10 10:12
–	12	((("metal/insulator/semiconductor") or ("metal-insulator-semiconductor")or ("MIS") or ("MAIS")) same (("C-V") or (CV) or (capacit$4 adj voltage) or (capacit$4-voltage) or (capacit$4/voltage)) and characteristic$5 and capacit$5) and synthesis	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/09 14:35
–	53	((("metal/insulator/semiconductor") or ("metal-insulator-semiconductor")or ("MIS") or ("MAIS")) same (("C-V") or (CV) or (capacit$4 adj voltage) or (capacit$4-voltage) or (capacit$4/voltage)) and characteristic$5 and capacit$5) and "nm"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/09 14:43
–	1	5233291.pn. and "MIS"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/09 15:29
–	2	5233292.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/09 15:30
–	2	5233291.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/09 15:43
–	0	((("metal/insulator/semiconductor") or ("metal-insulator-semiconductor")or ("MIS") or ("MAIS")) same (("C-V") or (CV) or (capacit$4 adj voltage) or (capacit$4-voltage) or (capacit$4/voltage)) and characteristic$5 and capacit$5) and (("4083254".PN. or three) adj nm)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/09 15:44
–	9	(("4083254".PN. or three) adj nm)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/10 07:14
–	1	5233291.pn. and MIS	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/10 07:27
–	6860	motohiro.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/10 07:27

–	6828	motohiro.inv.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/10 07:28
–	6	motohiro.inv. and ("MAIS")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/10 07:50
–	6	motohiro.inv. and ("MAIS")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/10 07:50
–	0	5233291.pn. and synthesis	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/10 10:08
–	0	5233291.pn. and switch$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/10 10:11
–	0	5233291.pn. and select$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/10 10:12
–	155	(("metal/insulator/semiconductor") or ("metal-insulator-semiconductor")or ("MIS") or ("MAIS")) same (("C-V") or (CV) or (capacit$4 adj voltage) or (capacit$4-voltage) or (capacit$4/voltage)) and characteristic$5 and capacit$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/10 10:13
–	107	((("metal/insulator/semiconductor") or ("metal-insulator-semiconductor")or ("MIS") or ("MAIS")) same (("C-V") or (CV) or (capacit$4 adj voltage) or (capacit$4-voltage) or (capacit$4/voltage)) and characteristic$5 and capacit$5) and (switch$5 or select$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/10 10:15
–	54	((("metal/insulator/semiconductor") or ("metal-insulator-semiconductor")or ("MIS") or ("MAIS")) same (("C-V") or (CV) or (capacit$4 adj voltage) or (capacit$4-voltage) or (capacit$4/voltage)) and characteristic$5 and capacit$5) and ((switch$5 or select$5) same (capacit$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/10 10:28
–	122	((("metal/insulator/semiconductor") or ("metal-insulator-semiconductor")or ("MIS") or ("MAIS")) same (("C-V") or (CV) or (capacit$4 adj voltage) or (capacit$4-voltage) or (capacit$4/voltage)) and characteristic$5 and capacit$5) and ((switch$5 or select$5 or elect$5) same (capacit$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/10 10:30

-	68	(((("metal/insulator/semiconductor") or ("metal-insulator-semiconductor")or ("MIS") or ("MAIS")) same (("C-V") or (CV) or (capacit$4 adj voltage) or (capacit$4-voltage) or (capacit$4/voltage)) and characteristic$5 and capacit$5) and ((switch$5 or select$5 or elect$5) same (capacit$5))) not (((("metal/insulator/semiconductor") or ("metal-insulator-semiconductor")or ("MIS") or ("MAIS")) same (("C-V") or (CV) or (capacit$4 adj voltage) or (capacit$4-voltage) or (capacit$4/voltage)) and characteristic$5 and capacit$5) and ((switch$5 or select$5) same (capacit$5)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/10 10:54
-	31	((silicon adj oxide) near2 thickness) near2 (("3" or three) adj "nm")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/10 10:57
-	13	(((silicon adj oxide) near2 thickness) near2 (("3" or three) adj "nm")) and @ad<20001212	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/10 11:15
-	6	((((silicon adj oxide) near2 thickness) near2 (("3" or three) adj "nm")) and @ad<20001212) and capacit$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/10 11:24
-	2	jp-11150246-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/10 12:46
-	1	("5233291").PN.	USPAT; US-PGPUB	2002/12/10 13:07
-	1	("4510516").PN.	USPAT; US-PGPUB	2002/12/10 13:10
-	1	("5568252").PN.	USPAT; US-PGPUB	2002/12/10 13:14
-	1	("5266892").PN.	USPAT; US-PGPUB	2002/12/10 13:16
-	1	("5360989").PN.	USPAT; US-PGPUB	2002/12/10 13:17
-	1	("3646527").PN.	USPAT; US-PGPUB	2002/12/10 13:17
-	2	(("5654588") or ("5973504")).PN.	USPAT	2004/02/17 14:44
-	0	5654588.pn. and (silicon near3 oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/18 14:52
-	0	5654588.pn. and (silicon near3 thickness)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/18 14:52
-	0	5654588.pn. and (silicon same thickness)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/18 14:52
-	1	5654588.pn. and (thickness)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/18 14:52